



NTP13N10 Information



For Reference Only

Part Number NTP13N10

Manufacturer ON Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 13A TO220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

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NTP13N10 Specifications

Manufacturer Part Number Manufacturer Category Discrete Semiconductor Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type N-Channel Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds NOSFET (Metal Oxide) 10V 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single TO-220-3 Series - ID-220-3 N-Channel N-Channel NOSFET (Metal Oxide) 100V 100V 200V 13A (Ta) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds
Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 13A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 550pF @ 25V
Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 13A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds TO-220-3 TO-220-3 TO-220-3 AV AV Ball Oxide) 10V 4V @ 250μA 550pF @ 25V
Series - N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 13A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 20nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 550pF @ 25V
FET Type Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 13A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds N-Channel NOSFET (Metal Oxide) 100V 13A (Ta) 20V 4V @ 250μA 550pF @ 25V
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 13A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds MOSFET (Metal Oxide) 10V 44V @ 250μA 550pF @ 25V
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C13A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs20nC @ 10VInput Capacitance (Ciss) (Max) @ Vds550pF @ 25V
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Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 20nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 550pF @ 25V
Gate Charge (Qg) (Max) @ Vgs 20nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 550pF @ 25V
Input Capacitance (Ciss) (Max) @ Vds 550pF @ 25V
77 (74)
$Vgs (Max)$ $\pm 20V$
FET Feature -
Power Dissipation (Max) 64.7W (Tc)
Rds On (Max) @ Id, Vgs 165 mOhm @ 6.5A, 10V
Operating Temperature $-55^{\circ}\text{C} \sim 175^{\circ}\text{C} \text{ (TJ)}$
Mounting Type Through Hole
Supplier Device Package TO-220AB
Package / Case TO-220-3
Report errors

NTP13N10 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NTP13N10 Payment Methods









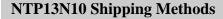
























If you have any question about NTP13N10, please do not hesitate to contact us!

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